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STMicroelectronics STTH806DTI

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STTH806DTI

Tandem 600 V hyperfast boost diode

I _{F(AV)}	8 A
V _{RRM}	600 V
T _{j (max)}	150° C
V _{F (max)}	2.24 V
I _{RM (typ.)}	4 A
t _{rr (typ.)}	13 ns

Table 1. Main product characteristics

Features and benefits

- Especially suited as boost diode in continuous mode power factor correctors and hard switching conditions
- Designed for high di/dt operation. Hyperfast recovery current to compete with SiC devices. Allows downsizing of mosfet and heatsinks
- Internal ceramic insulated devices with equal thermal conditions for both 300 V diodes
- Insulation (2500 V_{RMS}) allows placement on same heatsink as mosfet and flexible heatsinking on common or separate heatsink
- Static and dynamic equilibrium of internal diodes are warranted by design
- Package Capacitance: C = 7 pF



Description

The TURBOSWITCH "H" is an ultra high performance diode composed of two 300 V dice in series. TURBOSWITCH "H" family drastically cuts losses in the associated MOSFET when run at high dI_F/dt .

Table 2.Order codes

Part number	Marking
STTH806DTI	STTH806DTI

Table 3.	Absolute ratings	(limiting values)
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Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	600	V
I _{F(RMS)}	RMS forward voltage	14	А
I _{FSM}	Surge non repetitive forward current	180	А
T _{stg}	Storage temperature range	-65 to + 150	° C
Тj	Maximum operating junction temperature	150	°C

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Table 4. Thermal parameter

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case thermal resistance	2.6	°C/W

Table 5. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I_ (1)	Povorao lookago ourront	$T_j = 25^\circ C$	<u> </u>			10	
IR V Heverse leakage current	T _j = 125° C	VR = VRRM		15	100		
V_ (2)	Forward voltage drop	$T_j = 25^\circ C$	L QA			3.6	V
v F (=)	Forward voltage drop	T _i = 150° C	IF = 0 A		1.95	2.4	v

1. Pulse test: tp = 100 ms, δ < 2%

2. Pulse test: tp = 380 μ s, δ < 2%

To evaluate the conduction losses use the following equation: P = 1.7 x $I_{F(AV)}$ + 0.087 ${I_F}^2_{(RMS)}$

Table 6.Dynamic characteristics

Symbol	Parameter	Test conditions			Тур	Max	Unit	
			$I_{F} = 0.5 \text{ A}, I_{rr} = 0.25 \text{ A}, I_{R} = 1 \text{ A}$		13			
t _{rr}	Reverse recovery time	T _j = 25° C	I _F = 1 A, dI _F /dt = - 50 A/µs V _R = 30 V			30	ns	
I _{RM}	Reverse recovery current				4	5.5		
S	Reverse recovery softness factor	T _j = 125° C	T _j = 125° C	I _F = 8 A, V _R = 400, VdI⊏/dt = - 200 A/us		0.4		А
Q _{rr}	Reverse recovery charges		VarF/at = - 200 A/µS		50			

 Table 7.
 Turn-on switching characteristics

Symbol	Parameter	Test conditions			Тур	Max.	Unit
t _{fr}	Forward recovery time	$T_j = 25^\circ C$	I _F = 8 A, dI _F /dt = 100 A/μs V _{FR} = 1.1 x V _F max			200	ns
V _{FP}	Forward recovery voltage	$T_j = 25^\circ C$	I _F = 8 A, dI _F /dt = 100 A/μs			7	V



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Figure 3. **Relative variation of thermal** impedance junction to case versus pulse duration



Figure 4. Peak reverse recovery current versus dl_F/dt (typical values)



Reverse recovery time versus dl_F/dt Figure 6. Figure 5. (typical values)

Reverse charges versus dl_F/dt (typical values)





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Figure 9. Transient peak forward voltage versus dI_F/dt (typical values)

Figure 10. Forward recovery time versus dl_F/dt (typical values)







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Package information

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- Epoxy meets UL94, V0
- Cooling method: C
- Recommended torque value: 0.4 to 0.6 Nm

Table 8. TO-220AC insulated dimensions

					Dimer	nsions		
		Ref.	Mi	illimete	rs		Inches	
			Min.	Тур.	Max.	Min.	Тур.	Max.
		А	15.20		15.90	0.598		0.625
	с	a1		3.75			0.147	
	b2	a2	13.00		14.00	0.511		0.551
		В	10.00		10.40	0.393		0.409
		b1	0.61		0.88	0.024		0.034
	€2	b2	1.23		1.32	0.048		0.051
		С	4.40		4.60	0.173		0.181
<u>↓</u> a1		c1	0.49		0.70	0.019		0.027
l2a2		c2	2.40		2.72	0.094		0.107
		е	4.80		5.40	0.189		0.212
↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓ ↓		F	6.20		6.60	0.244		0.259
e		ØI	3.75		3.85	0.147		0.151
		14	15.80	16.40	16.80	0.622	0.646	0.661
		L	2.65		2.95	0.104		0.116
		12	1.14		1.70	0.044		0.066
		М		2.60			0.102	

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

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Ordering information

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Table 9.Ordering information

Part number	Marking	Package	Weight	Base qty	Delivery mode
STTH806DTI	STTH806DTI	TO-220AC	2.3 g	50	Tube

4 Revision history

Date	Revision	Changes
Oct-2003	2A	Initial release
May-2004	3	Reformatted
29-Jun-2005	4	Corrections to typographical errors. No technical changes.
11-Jul-2007	5	Reformatted to current standards. Removed I _{PEAK} parameter from <i>Table 3: Absolute ratings (limiting values)</i> .

Table 10. Revision history



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